## Nanoscale physics

## Properties of Doped GaSb Whiskers at Low Temperature

## <u>I.I. Khytruk<sup>1</sup></u>, A.A. Druzhinin<sup>1,2</sup>, I.P.Ostrovskii <sup>1,2</sup> Yu.N.Khoverko<sup>1,2</sup> N.S. Liakh-Kaguy<sup>1</sup>

<sup>1</sup>Lviv Polytechnic National University, S. Bander Str 12., 79013, Lviv, Ukraine E-mail: i.xytruk@gmail.com

<sup>2</sup> International Laboratory of High Magnetic Fields and Low Temperatures, Gajowicka 95, Wroclaw, Poland

Temperature dependencies of n-type GaSb whisker resistance was measured in temperature range 1,5–300 K and magnetic field up to 1 T. The peculiarities of whisker resistance in the low temperature range (sharp drop of the whisker resistance at about 4,2 K) were observed.

Fig.1. Magnetic field dependence of magnetoresistance for GaSb whiskers at various fixed temperatures

The changes of the magnetoresistance in magnetic field for GaSb whiskers at various fixed temperatures is presented at Fig.1.

To check the cause of electron localization one can suppose an existence of superconductance state in the whiskers taking into account the data of [1-2].

The possible reason of superconductivity in the whiskers could be appearance of weak antilocalization which leads to emergence the negative magnetoresistance. It was found that the magnetoresistance of these whiskers in low field regime can be described by two-dimensional weak antilocalization (2D WAL) model.

1. S. Matsuo, T. Koyama, K. Shimamura, T. Arakawa, Y. Nishihara, D. Chiba, K. Kobayashi, T. Ono, C. Z. Chang, K. He, X. C. Ma, and Q. K. Xue. Weak antilocalization and conductance fluctuation in a submicrometer-sized wire of epitaxial Bi2Se3// Physical Review B 2012. - 85, 075440.

2. D. D. Bykanov, S. V. Novikov, T. A. Polyanskaya, I. G. Savel'ev. Weak antilocalization and spin-orbit interaction in a In0.53Ga0.47As/InP quantum well in the persistent photoconductivity state.// Semiconductors.-2002.-**36**(12).-P. 1389-1397.